

COMPOUND SEMICONDUCTOR OPTOELECTRONIC DEVICE

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a compound semiconductor
5 optoelectronic device is proposed. There are steps of : forming an
optoelectronic device epitaxial wafer, the optoelectronic device epitaxial
wafer containing a V-shaped pit due to threading dislocation; forming
an insulated isolation material in the V-shaped pit of the optoelectronic
device epitaxial wafer; and forming an electrode layer on the
10 optoelectronic device epitaxial wafer having the insulated isolation
material in the V-shaped pit for completing the optoelectronic device.